Amendments to the Claims

1.   (currently amended) A method of fabricating a photomask that facilitates accurate measurement of a critical dimension on the photomask, comprising:

forming a first pattern on a substrate in a first area;

forming at least one test pattern on the substrate outside of the first area, wherein said at least one test pattern is <u>formed by duplicating a portion of the first pattern, said at least one test pattern</u> representative of the critical dimension on the photomask; and

attaching a pellicle to the substrate, wherein the pellicle covers the first area, but does not cover the at least one test pattern.

2.   (canceled)

3.   (currently amended) The method of claim <u>1</u> 2, wherein duplicating a portion of the first pattern as the at least one test pattern includes using optical proximity correction in the at least one test pattern.

4.   (previously presented) The method of claim 3, wherein using optical proximity correction includes using shapes selected from the group consisting of serifs, hammerheads and scattering bars.

5.   (currently amended) The method of claim 1, wherein forming the first pattern and forming the at least one test pattern include forming the first pattern and the at least one test pattern ~~substantially simultaneously~~ on the substrate <u>at the same time</u>.

6.   (currently amended) The method of claim 1, wherein forming the first pattern and forming the at least one test pattern <u>occur</u> ~~include forming the first pattern and the at least one test pattern~~ under ~~substantially~~ the same <u>or similar</u> conditions.

7.   (currently amended) A photomask that facilitates accurate measurement of a critical dimension on the photomask, comprising:

a substrate;

a first pattern formed on the substrate;

at least one test pattern formed on the substrate, wherein said at least one test pattern is <u>derived from a portion of the first pattern, said at least one test pattern</u> representative of the critical dimension on the photomask; and

a pellicle attached to the substrate, wherein the pellicle is not attached over the at least one test pattern.

8.   (canceled)

9.   (previously presented) The photomask of claim 7, wherein the at least one test pattern includes optical proximity correction.

10.   (original) The photomask of claim 9, wherein the optical proximity correction includes shapes selected from the group consisting of serifs, hammerheads and scattering bars.

11.   (original) The photomask of claim 7, wherein the photomask is a binary chrome-on-glass mask.

12.   (original) The photomask of claim 7, wherein the photomask is a phase shifting mask.

13.   (canceled)

14.   (previously presented) The method of claim 1, wherein the at least one test pattern includes patterns typical of the first pattern.

15.   (previously presented) The photomask of claim 7, wherein the at least one test pattern includes patterns typical of the first pattern.